

Antonella Poggi

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

84
papers

662
citations

15
h-index

21
g-index

85
ext. papers

706
ext. citations

1.7
avg, IF

2.84
L-index

#	Paper	IF	Citations
84	Radiation hardness after very high neutron irradiation of minimum ionizing particle detectors based on 4H-SiC p/sup +/n junctions. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 1557-1563	1.7	47
83	Permeated porous silicon for hydrocarbon sensor fabrication. <i>Sensors and Actuators A: Physical</i> , 1999 , 74, 95-99	3.9	42
82	Nitrogen Implantation to Improve Electron Channel Mobility in 4H-SiC MOSFET. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 961-967	2.9	38
81	Growth and Characterization of 3C-SiC Films for Micro Electro Mechanical Systems (MEMS) Applications. <i>Crystal Growth and Design</i> , 2009 , 9, 4852-4859	3.5	32
80	Composition and structure of tin/vanadium oxide surfaces for chemical sensing applications. <i>Sensors and Actuators B: Chemical</i> , 2000 , 71, 123-126	8.5	32
79	Analysis of electron traps at the 4HβSiC/SiO ₂ interface; influence by nitrogen implantation prior to wet oxidation. <i>Journal of Applied Physics</i> , 2010 , 108, 024503	2.5	25
78	Improved electrical characterization of Al/Ti ohmic contacts on p-type ion implanted 6H-SiC. <i>Semiconductor Science and Technology</i> , 2003 , 18, 554-559	1.8	25
77	TEM characterisation of porous silicon. <i>Micron</i> , 2000 , 31, 223-30	2.3	24
76	Effects of heating ramp rates on the characteristics of Al implanted 4HβSiC junctions. <i>Applied Physics Letters</i> , 2006 , 88, 162106	3.4	23
75	Thick oxidised porous silicon layer as a thermo-insulating membrane for high-temperature operating thin- and thick-film gas sensors. <i>Sensors and Actuators B: Chemical</i> , 1998 , 49, 22-29	8.5	21
74	MOS capacitors obtained by wet oxidation of n-type 4HβSiC pre-implanted with nitrogen. <i>Microelectronic Engineering</i> , 2007 , 84, 2804-2809	2.5	18
73	Permeated Porous Silicon Suspended Membrane as Sub-ppm Benzene Sensor for Air Quality Monitoring. <i>Journal of Porous Materials</i> , 2000 , 7, 197-200	2.4	17
72	Porous silicon layer permeated with Sn ^{IV} mixed oxides for hydrocarbon sensor fabrication. <i>Thin Solid Films</i> , 1997 , 297, 43-47	2.2	16
71	Effect of nitrogen implantation at the SiO ₂ /SiC interface on the electron mobility and free carrier density in 4H-SiC metal oxide semiconductor field effect transistor channel. <i>Journal of Applied Physics</i> , 2010 , 107, 044506	2.5	15
70	Investigation on the use of nitrogen implantation to improve the performance of n-channel enhancement 4H-SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2021-2028	2.9	15
69	Low temperature oxidation of SiC preamorphized by ion implantation. <i>Journal of Applied Physics</i> , 2004 , 95, 6119-6123	2.5	14
68	Contact Resistivity and Barrier Height of Al/Ti Ohmic Contacts on p-Type Ion Implanted 4H- and 6H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 881-884	0.4	13

67	Oxidation kinetics of ion-amorphized (0001) 6H-SiC: Competition between oxidation and recrystallization processes. <i>Applied Physics Letters</i> , 2005 , 86, 121907	3.4	12
66	Measurements and simulations of charge collection efficiency of p+/n junction SiC detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2005 , 546, 218-221	1.2	11
65	A Comparative Study of High-Temperature Aluminum Post-Implantation Annealing in 6H- and 4H-SiC, Non-Uniform Temperature Effects. <i>Materials Science Forum</i> , 2002 , 389-393, 827-830	0.4	11
64	Contact resistivity of Al/Ti ohmic contacts on p-type ion implanted 4H- and 6H-SiC.. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 742, 621		11
63	microstructural development in pure and V-doped SnO ₂ nanopowders. <i>Journal of the European Ceramic Society</i> , 1999 , 19, 2073-2077	6	11
62	Structural Characterization of Alloyed Al/Ti and Ti Contacts on SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 837-840	0.4	10
61	Lattice disorder and recombination centres in heat-treated FZ silicon. <i>Physica Status Solidi A</i> , 1985 , 92, 177-185		9
60	Annealing effects on leakage current and epilayer doping concentration of p+n junction 4H-SiC diodes after very high neutron irradiation. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2007 , 583, 173-176	1.2	8
59	Measurements of Charge Collection Efficiency of p+/n Junction SiC Detectors. <i>Materials Science Forum</i> , 2005 , 483-485, 1021-1024	0.4	8
58	Low-Temperature Thermal Oxidation of Ion-Amorphized 6H-SiC. <i>Materials Science Forum</i> , 2002 , 389-393, 1109-1112	0.4	8
57	Deep level transient spectroscopy study of the damage induced in n-type silicon by a gate oxide etching in a CHF ₃ /Ar plasma. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 623		7
56	Al/Ti Ohmic Contacts to p-Type Ion-Implanted 6H-SiC: Mono- and Two- Dimensional Analysis of TLM Data. <i>Materials Science Forum</i> , 2003 , 433-436, 673-676	0.4	7
55	Current Analysis of Ion Implanted p+/n 4H-SiC Junctions: Post-Implantation Annealing in Ar Ambient. <i>Materials Science Forum</i> , 2006 , 527-529, 815-818	0.4	6
54	Interfacial Properties of SiO ₂ Grown on 4H-SiC: Comparison between N ₂ O and Wet O ₂ Oxidation Ambient. <i>Materials Science Forum</i> , 2006 , 527-529, 979-982	0.4	6
53	Rapid Thermal Annealing of p-Type Silicon: Correlation Between Deep-Level Transient Spectroscopy and Lifetime Measurements. <i>Journal of the Electrochemical Society</i> , 1994 , 141, 754-758	3.9	6
52	Copper impurities and their annealing behaviour in FZ silicon. <i>Physica Status Solidi A</i> , 1994 , 143, 373-377		6
51	Boron ion implantation through Mo and Mo silicide layers for shallow junction formation. <i>Journal of Applied Physics</i> , 1991 , 69, 3962-3967	2.5	6
50	Schottky contact barrier height enhancement on p-type silicon by wet chemical etching. <i>Applied Physics A: Solids and Surfaces</i> , 1989 , 48, 391-395		6

49	Some electrical characteristics of Fe and its annealing behaviour in FZ silicon. <i>Physica Status Solidi A</i> , 1990 , 118, 491-496		6
48	Effects of Very High Neutron Fluence Irradiation on p+n Junction 4H-SiC Diodes. <i>Materials Science Forum</i> , 2007 , 556-557, 917-920	0.4	5
47	SiC Donor Doping by 300°C P Implantation: Characterization of the Doped Layer Properties in Dependence of the Post-Implantation Annealing Temperature. <i>Materials Science Forum</i> , 2004 , 457-460, 945-950	0.4	5
46	Electrical Properties of Rapid Thermal Annealing Induced Defects in Silicon. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 2081-2085	3.9	5
45	Rapid screening and identification of illicit drugs by IR absorption spectroscopy and gas chromatography 2013 ,		4
44	Non-Nitridated Oxides: Abnormal Behaviour of N-4H-SiC/SiO ₂ Capacitors at Low Temperature Caused by near Interface States. <i>Materials Science Forum</i> , 2011 , 679-680, 346-349	0.4	4
43	Ion Implanted p+/n 4H-SiC Junctions: effect of the Heating Rate during Post Implantation Annealing. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 1		4
42	Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. <i>Materials Science Forum</i> , 2007 , 556-557, 639-642	0.4	4
41	Extraction of the Schottky Barrier Height for Ti/Al Contacts on 4H-SiC from I-V and C-V Measurements. <i>Materials Science Forum</i> , 2004 , 457-460, 993-996	0.4	4
40	The electrical activity of stacking faults in Czochralski silicon. <i>Applied Physics A: Solids and Surfaces</i> , 1989 , 48, 431-436		4
39	Electrical Properties of Silver Impurities and their Annealing Behaviour in p-Type Fz Silicon. <i>Journal De Physique III</i> , 1996 , 6, 1691-1696		4
38	Residual Stress Measurement and Simulation of 3C-SiC Single and Poly Crystal Cantilevers. <i>Materials Science Forum</i> , 2010 , 645-648, 865-868	0.4	3
37	Fabrication of MOS Capacitors by Wet Oxidation of p-Type 4H-SiC Preamorphized by Nitrogen Ion Implantation. <i>Materials Science Forum</i> , 2007 , 556-557, 651-654	0.4	3
36	Ni-Silicide Contacts to 6H-SiC: Contact Resistivity and Barrier Height on Ion Implanted n-Type and Barrier Height on p-Type Epilayer. <i>Materials Science Forum</i> , 2005 , 483-485, 737-740	0.4	3
35	Study of the electrical active defects induced by reactive ion etching in n-type silicon. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995 , 13, 2139		3
34	Effect of Rapid Thermal Annealing on Electrical and Structural Properties of Silicon. <i>Journal of the Electrochemical Society</i> , 1991 , 138, 1841-1845	3.9	3
33	Denuded zone stability in a SPAD diode as a function of out-diffusion parameters. <i>IEEE Transactions on Electron Devices</i> , 1987 , 34, 1496-1500	2.9	3
32	Processing-Induced Electrically Active Defects in Black Silicon Nanowire Devices. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 10443-50	9.5	2

31	Nitridation of the SiO ₂ /SiC Interface by N ⁺ Implantation: Hall versus Field Effect Mobility in n-Channel Planar 4H-SiC MOSFETs. <i>Materials Science Forum</i> , 2010 , 645-648, 491-494	0.4	2
30	Correlation between Current Transport and Defects in n+/p 6H-SiC Diodes. <i>Materials Science Forum</i> , 2006 , 527-529, 811-814	0.4	2
29	Analysis of the Electrical Activation of P ⁺ Implanted Layers as a Function of the Heating Rate of the Annealing Process. <i>Materials Science Forum</i> , 2007 , 556-557, 571-574	0.4	2
28	Ar Annealing at 1600°C and 1650°C of Al ⁺ Implanted p+/n 4H-SiC Diodes: Analysis of the J-V Characteristics Versus Annealing Temperature. <i>Materials Science Forum</i> , 2005 , 483-485, 625-628	0.4	2
27	Surface damage in processed silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1996 , 42, 249-253	3.1	2
26	RTA-induced defects: a comparison between lamp and electron beam techniques. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989 , 4, 231-235	3.1	2
25	Intrinsic gettering of Cr impurities in p-type Cz silicon. <i>Physica Status Solidi A</i> , 1990 , 121, 181-185		2
24	Lifetime and crystal order in annealed CZ silicon. <i>Physica Status Solidi A</i> , 1988 , 108, 503-508		2
23	SiC NWs Grown on Patterned and MEMS Silicon Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 508-511	0.4	1
22	The Influence of Excess Nitrogen, on the Electrical Properties of the 4H-SiC/SiO ₂ Interface. <i>Materials Science Forum</i> , 2011 , 679-680, 326-329	0.4	1
21	Improvement of Electron Channel Mobility in 4H SiC MOSFET by Using Nitrogen Implantation. <i>Materials Science Forum</i> , 2008 , 600-603, 699-702	0.4	1
20	Room Temperature Annealing Effects on Leakage Current of Ion Implanted p+n 4H-SiC Diodes. <i>Materials Science Forum</i> , 2008 , 600-603, 1027-1030	0.4	1
19	Minimum Ionizing Particle Detector Based on p+n Junction SiC Diode. <i>Materials Science Forum</i> , 2006 , 527-529, 1469-1472	0.4	1
18	The Role of the Ion Implanted Emitter State on 6H-SiC Power Diodes Behavior. A Statistical Study. <i>Materials Science Forum</i> , 2004 , 457-460, 1025-1028	0.4	1
17	Characterization of a Thermal Oxidation Process on SiC Preamorphized by Ar Ion Implantation. <i>Materials Science Forum</i> , 2004 , 457-460, 1357-1360	0.4	1
16	n+/p Diodes Realized in SiC by Phosphorus Ion Implantation: Electrical Characterization as a Function of Temperature. <i>Materials Science Forum</i> , 2005 , 483-485, 649-652	0.4	1
15	Arsenic ion implantation through Mo and Mo silicide layers for shallow junction formation. <i>Solid-State Electronics</i> , 1992 , 35, 941-947	1.7	1
14	Shallow junction formation using MoSi ₂ as diffusion source. <i>Microelectronic Engineering</i> , 1992 , 19, 673-676		1

- 13 Effect of passivating oxides on the surface recombination velocity in silicon. *Physica Status Solidi A*, **1989**, 113, K61-K65 1
- 12 Passivation by N Implantation of the SiO₂/SiC Acceptor Interface States: Impact on the Oxide Hole Traps and the Gate Oxide Reliability. *Materials Research Society Symposia Proceedings*, **2010**, 1246, 1
- 11 Analysis of the Electron Traps at the 4H-SiC/SiO₂ Interface of a Gate Oxide Obtained by Wet Oxidation of a Nitrogen Pre-Implanted Layer. *Materials Science Forum*, **2009**, 615-617, 533-536 0.4
- 10 Characterization of Phosphorus Implanted n+/p Junctions Integrated as Source/Drain Regions in a 4H-SiC n-MOSFET. *Materials Science Forum*, **2009**, 615-617, 687-690 0.4
- 9 Effects of N Implantation before Gate Oxidation on the Performance of 4H-SiC MOSFET. *Materials Science Forum*, **2009**, 615-617, 761-764 0.4
- 8 C-V and DLTS Analyses of Trap-Induced Graded Junctions: The Case of Al⁺ Implanted JTE p+n 4H-SiC Diodes. *Materials Science Forum*, **2009**, 615-617, 469-472 0.4
- 7 Epitaxial Growth, Mechanical, Electrical Properties of SiC/Si and SiC/Poli-Si. *Materials Science Forum*, **2012**, 717-720, 897-900 0.4
- 6 Ion Implanted p+/n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. *Materials Science Forum*, **2006**, 527-529, 819-822 0.4
- 5 Competition between Oxidation and Recrystallization in Ion Amorphized (0001) 6H-SiC. *Materials Science Forum*, **2005**, 483-485, 665-668 0.4
- 4 On the Connection Between Interstitial Oxygen, Oxygen Precipitate, and Diffusions of Cr and Cu Impurities in Cz Silicon. *Physica Status Solidi A*, **1991**, 123, K1-K6
- 3 B-Ion Implantation into Mo-Film for Shallow Junction Formation: DLTS Analyses on the p+/n Fabricated Diodes. *Solid State Phenomena*, **1991**, 19-20, 505-510 0.4
- 2 The Effects of High Temperature Anneal on the Electrical Activity of Iron in B-Doped Cz Silicon. *Physica Status Solidi A*, **1989**, 114, 247-252
- 1 Effects of silicon ion-beam mixing on p+/n diodes: DLTS analyses of the induced defects. *Physica Status Solidi A*, **1990**, 121, K135-K139